

AIN SHAMS UNIVERSITY FACULTY OF ENGINEERING CAIRO – EGYPT

RF Front End for LTE Receiver

A Thesis

Submitted in partial fulfillment for the requirements of the degree of
Master of Science in Electrical Engineering
Electronics and Communications Engineering Department
Ain Shams University

Submitted by

Eng. Dalia Hussein Sadek Kamal

Supervised by

Prof. Dr. Abdelhalim Abdelnabi Zekry

Ain Shams University

Dr. Heba A. Shawkey

Electronics Research Institute (ERI)

November 2015



Examiners Committee

Name: Dalia Hussein Sadek Kamal

Thesis: RF Front End for LTE Receiver.

Degree: Master of Science in Electrical Engineering		
Title, Name and Affiliation	Signature	
1. Prof. Dr. Mohamed Abd Elmoneam Abouelela Electronics and Communications Eng. Dept. Faculty of Engineering – Future University		
 Prof. Dr. Wagdy Refat Anis Electronics and Communications Eng. Dept. Faculty of Engineering - Ain Shams University 		
3. Prof. Dr. Abdelhalim Abdelnaby Zekry Electronics and Communications Eng. Dept. Faculty of Engineering - Ain Shams University		
	Date:/ /	
	Date:/ /	

ACKNOWLEDGEMENTS

I start by thanking ALLAH for guiding me to accomplish this work and writing this thesis.

At the end of this long journey, many people come to mind who had helped me to complete my master study and this dissertation. First and foremost, I express my deepest gratitude and thanks to my advisors Prof. Dr. Abdelhalim Abdelnaby Zekry, and Dr. Heba A. Shawkey for their continuous supervision, support and their technical support throughout my graduate study. Many thanks to the microwave lab members- electronics research institute for their great help in measurement Prof. Dr. Ahmed Attia, Prof. Dr. Khaled Fawzy and Dr. Asmaa Farahat. This work could not be completed without their encouragement.

A great appreciate for my parents and my brothers for always encouraging and supporting me in whatever I do. I especially wish to thank my husband and my children for their patience and care during my long working hours.

STATEMENT

This Thesis is submitted to Ain Shams University in partial fulfillment of the

degree of Master of Science in Electrical Engineering.

The work included in this thesis was carried out by the author in the

Department of Electronics and Communications Engineering, Ain Shams

University.

No part of this Thesis has been submitted for a degree or a qualification at any

other university or institute.

Name: Dalia Hussein Sadek Kamal

Signature:

Date

iv

Published Papers

- 1. Dalia Sadek, Abdelhalim Zekry and Heba A. Shawkey," Passive Front End for LTE TDD Transceiver ", International Journal of Computer Applications, (0975-8887), Vol. 116-No.8, pp. 6-11 April, 2015.
- Dalia Sadek, Abdelhalim Zekry and Heba A. Shawkey, "Constructing Complete Radio Frequency Receiver for LTE TDD Transceiver", Communications on Applied Electronics, ISSN: 2394-4714 Foundation of Computer Science, FCS, New York, USA, Volume 3–No.2, October 2015

Abstract

The development of wireless communication systems into multi-standard radio architectures that can process a multitude of frequency bands and modulation schemes has led to a growing demand for wideband receiver front-ends. To allow for portability and low cost, these new architectures also need to be compact size, low power. These requirements have made the simple architecture of the Zero IF receiver, especially attractive for this application. The design of a Zero IF receiver that comply the new standards LTE meets several challenges. The new standards take advantage of the multi carrier modulation scheme OFDM to increase spectral efficiency, which demands for higher linearity because of a non-constant signal envelope. Zero IF architectures consist of two main parts, the first part is the passive one which consists of an antenna and band pass filter and the second part which is the active part consists of Low noise amplifier, demodulator and synthesizer. The frequency spectrum allocated for an LTE range from 700MHz to 2.7GHz.

This thesis focuses on the design and implementation of zero if LTE receiver operates at band 36 TDD (1930-1990) MHz. The proposed receiver consists of two parts a passive part, an antenna and hairpin filter and an active part which is the LNA, demodulator and frequency synthesizer.

The first goal is to design and fabricate the passive components of the front end receiver which are a microstrip patch antenna with defected ground structure and a third order hairpin band pass filter. The antenna and filter are analyzed using Computer Simulation Technology (CST) Microwave Studio. The proposed devices are fabricated using FR-4 material substrate. The overall dimensions of the antenna are 43mm x36mm x1. 6mm. the antenna operates between 1923 MHz to 1990 MHz for return loss -10 dB and covers LTE network band 2 FDD mode downlink and band 36 TDD mode. The simulation results were 2.67dBi directivity and1.242dB gain with omnidirectional radiation pattern, a return loss of -31.85dB at resonant frequency 1950 MHz and 70 MHz minimum bandwidth at -10 dB return loss.

The hairpin third order band pass filter with overall dimensions 38.6mm x32.16 mm x1.6mm, center frequency of 1950 MHz and -3dB BW of 90 MHz in addition to a fractional bandwidth of 4.615%. The filter covers LTE network band 36 (TDD).

The second goal that this thesis focuses is selecting a real made off-shelf components for the active part of the front end receiver which include Low noise amplifier, IQ demodulator and frequency synthesizer.

The third goal is combine the passive part with the active part to make a complete RF front end receiver for LTE, then test and measure the whole system. Scattering parameters are measured by using the Vector Network Analyzer (VNA) E8719A. The power measurements are made using Signal Analyzer N9010A, Agilent E8267D PSG Vector Signal Generator and Spectrum Analyzer. Measurements and simulations show good agreement. The receiver front-end is covering a bandwidth (1930-1990) MHz with a noise figure 4.022 dB and IIP3 of 2.65 dBm. The measured performance of the proposed receiver is compared with other receivers to prove its validity for LTE applications.

Table of contents

CHAPTER (1): INTRODUCTION

1.1 Overview	1
1.2 Introduction to Wireless Communication	1
1.3 THESIS OBJECTIVE AND ACHIEVEMENTS	3
1.4 Thesis Organization.	4
CHAPTER (2): LTE TECHNOLOGY	
2.1 Introduction.	6
2.2 WIRELESS STANDARD EVOLUTION.	6
2.2.1 First Generation (1G) – Analog System.	8
2.2.2 Second Generation (2G) Network – Digital System	9
2.2.3 2.5G Networks (GPRS)	9
2.2.4 3G Networks	9
2.2.5 4G Networks – Integration System	10
2.2.6 5G Networks - Real Wireless World System	12
2.3 LTE TECHNOLOGY.	13
2.3.1 OFDM Technology	13
2.3.2 MIMO Technology	13
2.3.3 New System Architecture Evolution (SAE)	14
2.4 LTE Specifications.	14
2.5 LTE BANDS OVERVIEW.	17
2.5.1 FDD LTE Frequency Band Allocations	17
2.5.2 TDD LTE Frequency Band Allocations	19
2.6 ADVANTAGES /DISADVANTAGES OF LTE TDD AND LTE FDD	20
2.7 Receiver Architectures	21
2.7.1 Super Heterodyne Receiver	21
2.7.2 Low-IF Receiver	22
2.7.3 Zero IF Receiver.	22
2.7.4 Band-Pass Sampling Receiver.	23
2.8 Conclusion	25

CHAPTER (3): PASSIVE RF FRONT END FOR LTE RECEIVER

3.1 Introduction.	26
3.2 ZERO IF LTE RECEIVER ARCHITECTURE	26
3.3 ZERO IF RECEIVER PASSIVE FRONT END.	27
3.3.1 Microstrip Patch Antenna	28
3.3.2 Feeding Techniques	29
3.3.3 Advantages and Disadvantages of Microstrip Patch Antenna	s30
3.3.4 Proposed Antenna Design	31
3.3.5 Antenna Simulation and Measurements	35
3.3.6 Microstrip Bandpass Filter	38
3.3.7 Hairpin-Line Bandpass Filters	39
3.3.8 Proposed Filter Design	39
3.3.9 Filter Simulation and Measurements	44
3.4 Conclusion.	45
CHAPTER (4): ACTIVE RF FRONT END FOR LTE RECEIVER	}
4.1 Introduction.	
4.2 Low Noise Amplifier (LNA).	
4.2.1 Main Parameters for Measuring Low Noise Amplifier	
4.2.1.1 Gain	
4.2.1.2 Noise Performance	
4.2.1.3 Linearity	
4.2.1.4 S-Parameters	
4.2.2 Low Noise Amplifier (LNA) Description	
4.2.3 LNA S-Parameters Measurement	
4.2.3.1 Gain.	
4.2.3.2 Return Loss and Reverse Isolation.	
4.2.4 Linearity Measurement	
4.3 FREQUENCY SYNTHESIZER	
4.3.1 Frequency Synthesizer Description	
4.3.1.1 Frequency Coverage Options	
4.3.1.2 VCO (N) DIVIDER.	
4.3.1.3 OUTPUT (O) DIVIDER	
4.3.2 Frequency Synthesizer Measurement	60

4.4 DIRECT CONVERSION I/Q DEMODULATOR	63
4.4.1 Main Specifications for Direct Conversion I/Q Demodulator	63
4.4.1.1 Conversion Gain or Loss	64
4.4.1.2 Input Intercept Point (IIP3)	64
4.4.1.3 Spurious Products	65
4.4.1.4 Isolation	65
4.4.1.5 Noise Figure (NF).	66
4.4.1.6 Operating Frequency Range	67
4.4.2 Direct Conversion I/Q Demodulator Description	67
4.4.3 The Direct Conversion I/Q Demodulator Measurement	68
4.4.4 Set Up for Measuring Direct Conversion I/Q Demodulator Using Tw	O
Signal Generators	68
4.4.5 Set Up for Measuring Direct Conversion I/Q Demodulator Using	
Frequency Synthesizer.	70
4.5 Conclusion.	72
CHAPTER (5): LTE RF FRONT END RECEIVER	
5.1 Introduction	74
5.2 KEY RF RECEIVER PERFORMANCE.	74
5.2.1 Receiver Sensitivity	74
5.2.2 Noise Figure	75
5.2.3 Dynamic Range	76
5.2.4 Channel Capacity	77
5.2.5 Receiver Selectivity	77
5.2.6 Linearity	78
5.3 COMPLETE RF RECEIVER MEASUREMENT	79
5.4 PERFORMANCE COMPARISON WITH RECENT PUBLICATIONS	86
5.5 Conclusion.	87
CHAPTER (6): CONCLUSIONS AND FUTURE WORK	
6.1 Introduction	88
6.2 Conclusions	88
6.3 FUTURE WORK	89

Table of Figures

Fig. 1.1 Wireless Standard Evolutions	2
Fig. 2.1 Evolution of Digital Cellular Standards	8
Fig. 2.2: Evolution to 3G	10
Fig. 2.3: LTE (a) DL and (b)UL Multiple Access Schemes (each color stands for	or one
user)	13
Fig. 2.4 : Super Heterodyne RF Receiver Architecture	21
Fig. 2.5 :Low-IF Receiver Architecture	22
Fig. 2.6: The Zero If Receiver Architecture	23
Fig. 2.7 : A Band-Pass Sampling Receiver Architecture	23
Fig. 3.1 : The Proposed Zero IF Receiver	26
Fig. 3.2: The Proposed Passive Front End Receiver Components	27
Fig. 3.3 : Structure of A Microstrip Patch Antenna	28
Fig. 3.4 : Common Shapes of Microstrip Patch Elements	29
Fig. 3.5 : Structure of A Micro-Strip Line Feed Antenna	31
Fig. 3.6: Conventional Antenna Design (a) Top View and (b) Bottom View	32
Fig. 3.7 Conventional Pattern Antenna Simulation	33
Fig. 3.8: Antenna Design (a) Top View (b) Bottom View	34
Fig. 3.9: Antenna Photography (a) Top View (b) Bottom View	35
Fig. 3.10: Comparison Between The Simulation and Measured Results for The	
Antenna	36
Fig. 3.11: Directivity =2.670 dBi at 1.95 GHz Center Frequency	37
Fig. 3.12 : Gain =1.242 dB at 1.95GHz Center Frequency	37
Fig. 3.13: Radiation Patterns of E-Plane and H- Plane at Frequency 1950 MHz,	(a) E-
Plane and (b) H-Plane	38
Fig. 3.14: Attenuation Characteristics for Chebyshev Lowpass Response	40
Fig. 3.15: Lowpass Prototype Filters For All-Pole Filters With A Ladder Netwo	rk
Structure	41
Fig. 3.16: Equivalent Circuit of The n-pole Hairpin Bandpass Filter	42
Fig. 3.17: Filter Design (a) Top View (b) Filter Photography	43
Fig. 3.18: Comparison Between The Simulation and Measured Results For The	
Hairpin Filter	45
Fig. 4.1: The Active Components Of The Proposed Front End Receiver	47

Fig. 4.2: 1dB Compression Point	19
Fig. 4.3 : Linearity Parameters of RF Receiver	50
Fig. 4.4: RF2442 Evaluation Board Schematic [40]5	51
Fig. 4.5 :The Measurement of S-parameters of a Low Noise Amplifier Using The	
Vector Network Analyzer (VNA) E8719A.	52
Fig. 4.6: LNA Gain Measurement	53
Fig. 4.7: LNA S-parameters (dB) Measurement	54
Fig. 4.8 : $P_{in}\left(dBm\right)$ Vs. $P_{out}\left(dBm\right)$ at frequencies 1920 MHz , 1950 MHz and 1980	
MHz5	55
Fig. 4.9: 1dB Compression Point at 1950 MHz	55
Fig. 4.10: Pout and Gain Vs. Pin at the Operating Frequency 1950MHz5	56
Fig. 4.11 : Basic Digital Frequency Synthesizer5	57
Fig. 4.12 : Wideband Receiver [43]	58
Fig. 4.13: Simplified LTC6946 Block Diagram With External Reference Clock and	1
Loop Filter [43]5	59
Fig. 4.14 : Photo of Measurement Equipment Setup	50
Fig. 4.15 Snapshot of The Loop Design Parameters of The PLL wizard Software Too	ol
at 1940MHz6	51
Fig. 4.16 Snapshot of The System Parameters of The PLL Wizard Software Tool $% \left\{ 1\right\} =\left\{ 1\right\}$	
1940MHz6	51
Fig. 4.17 : Proper Measurement Equipment Setup for Frequency Synthesizer	52
Fig. 4.18 : The RF Output of The Frequency Synthesizer at Frequency 1940 MHz on	
the Spectrum Analyzer (N9010A)	53
Fig. 4.19 : Third-Order Intercept Point	55
Fig. 4.20 : Image Noise and Image Filter	56
Fig. 4.21 : Direct Conversion Receiver with IIP2 and DC Offset Calibration [46]6	58
Fig. 4.22: LTC 5585 I/Q Demodulator Measurement Setup	59
Fig. 4.23 : The Photo of The IQ Demodulator Connected to Two Signal Generators.	59
Fig. 4.24 : The Measured Baseband Signal Output of The Demodulator	70
Fig. 4.25 : LTC 5585 I/Q Demodulator Measurement Setup Using Frequency	
Synthesizer	71
Fig. 4.26: Photo of IQ Demodulator With The Programmable Frequency Synthesize	er
7	71

Fig. 4.27: The Measured Baseband Signal Output of The IQ Demodulator Using	
Frequency Synthesizer	.72
Fig. 5.1 : Definitions of Dynamic Range Parameters	.76
Fig. 5.2: (a) Band Select Filter Reject Out of Band Interferes,(b) Channel Select	
Filter Reject Out of Channel Interferes	.77
Fig. 5.3: Inband Intermodulation Due To Nonlinearities In The Receiver Front-End	178
Fig. 5.4 : Gain Compression	.79
Fig. 5.5 : Photo of Setup for RF Receiver	.80
Fig. 5.6: Measurement Setup of RF Receiver	.81
Fig. 5.7: The Input Signal to RF Receiver	.82
Fig. 5.8 : The Output Signal From The RF Synthesizer	.82
Fig. 5.9: The Output Baseband Signal From The RF Receiver at 10 MHz	.83

List of Tables

Table 1.1: Performance Evolution of 3GPP Standards	3
Table 2.1 : LTE Release 8 Specification Overview	16
Table 2.2: The Specified Frequency Bands of FDD LTE and The Channel	
Bandwidths [15]	18
Table 2.3 : The Specified Frequency Bands of TDD LTE and The Channel \dots	19
Table 2.4 : Comparison of TDD Vs. FDD Duplex Format	20
Table 2.5 : Comparison of Receiver Architecture	24
Table 3.1 : Advantages and Disadvantage of Microstrip Antenna	30
Table 3.2 : Antenna Parameter's Size	33
Table 3.3 :E-Shape Antenna Parameter's Size	34
Table 3.4 : Lowpass Prototype Elements Values 3^{Th} Order Filter	41
Table 3.5 : Quality Factors and Mutual Coupling Coefficients	43
Table 3.6 : Filter Parameter's Size.	44
Table 4.1 : Output Frequency Range Vs Output Divider Setting (GHz)	58
Table 4.2 : DC1705b Requirements and Characteristics	62

List of Symbols

C_{gs} Gate-Source Capacitance

F_i Noise factor of the i stage

Gain of the i stage

g_i Normalized element of filter

g_m Transconductance

h Height of dielectric substrate (m)

I_D Drain Current

IIP3 Input Third Order Intercept Point

L_{Ar} Passband return loss

L_{AS} Stopband attenuation

OIP3 Output Third Order Intercept Point

P_{DC} Power Delivered from the DC Power Supply

P_{I1-dB} Input Referred 1-dB Compression Point (in dB)

P_{in} Power of The Input Signal

P_{O1-dB} Output Referred 1-dB Compression Point (in dB)

P_{out} Power of The Output Signal

S₁₁ Input Return Loss

S₁₂ Reverse Isolation

S₂₁ Power Gain

S₂₂ Output Return Loss

Tan δ Loss tangent

V_{DS} Drain-Source Voltage

V_{gs} Gate-Source Voltage

Z_{in} Input Impedance

Z₀ Characteristic Impedance

β Propagation Constant in Free Space

 $\varepsilon_{\rm eff}$ Relative Permittivity